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Kind regards,

Team Nexperia

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

Rev. 3 — 3 January 2012

Product data sheet

1. Product profile

1.1 General description

PNP/PNP Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number			NPN/PNP NPN/NPN		Package
	NXP	JEITA	complement	complement	configuration
PEMB10	SOT666	-	PEMD10	PEMH10	ultra small and flat lead
PUMB10	SOT363	SC-88	PUMD10	PUMH10	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio		17	21	26	



006aaa212

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

Pinning information 2.

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2	0	
5	input (base) TR2		
6	output (collector) TR1	001aab555	

Ordering information 3.

Table 4. **Ordering information**

Type number	Package			
	Name	Description	Version	
PEMB10	-	plastic surface-mounted package; 6 leads	SOT666	
PUMB10	SC-88	plastic surface-mounted package; 6 leads	SOT363	

Marking 4.

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMB10	Z5
PUMB10	B*0

[1] * = placeholder for manufacturing site code.

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

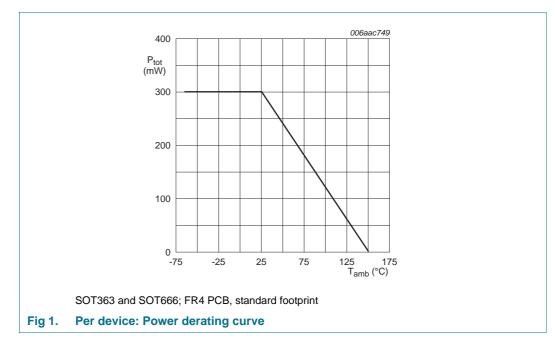
5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
VI	input voltage				
	positive		-	+5	V
	negative		-	-12	V
lo	output current		-	-100	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[1]		
	PEMB10 (SOT666)		[2] _	200	mW
	PUMB10 (SOT363)		-	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[1]		
	PEMB10 (SOT666)		[2] _	300	mW
	PUMB10 (SOT363)		-	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



6. Thermal characteristics

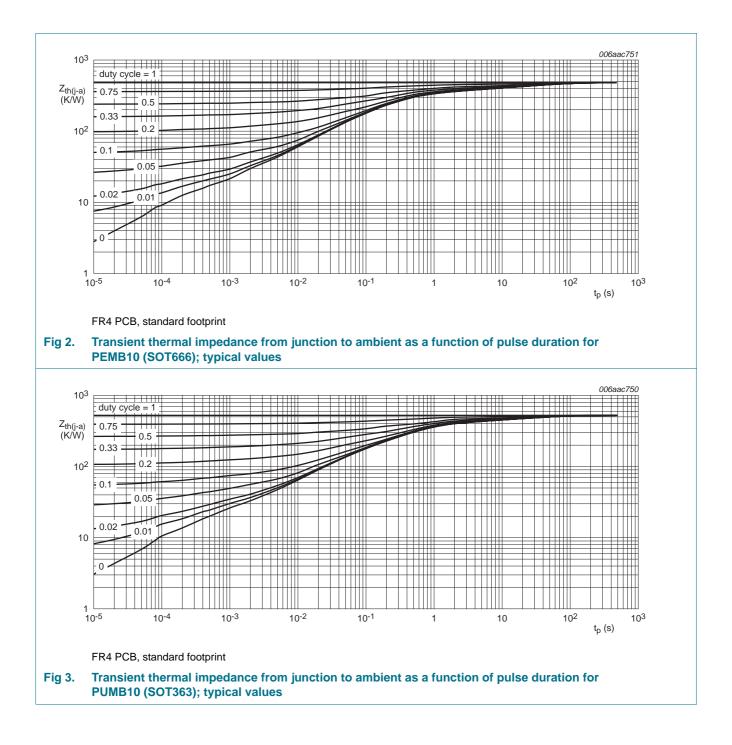
Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]			
	PEMB10 (SOT666)		[2] _	-	625	K/W
	PUMB10 (SOT363)		-	-	625	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	PEMB10 (SOT666)		[2] _	-	417	K/W
	PUMB10 (SOT363)		-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMB10; PUMB10

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

7. Characteristics

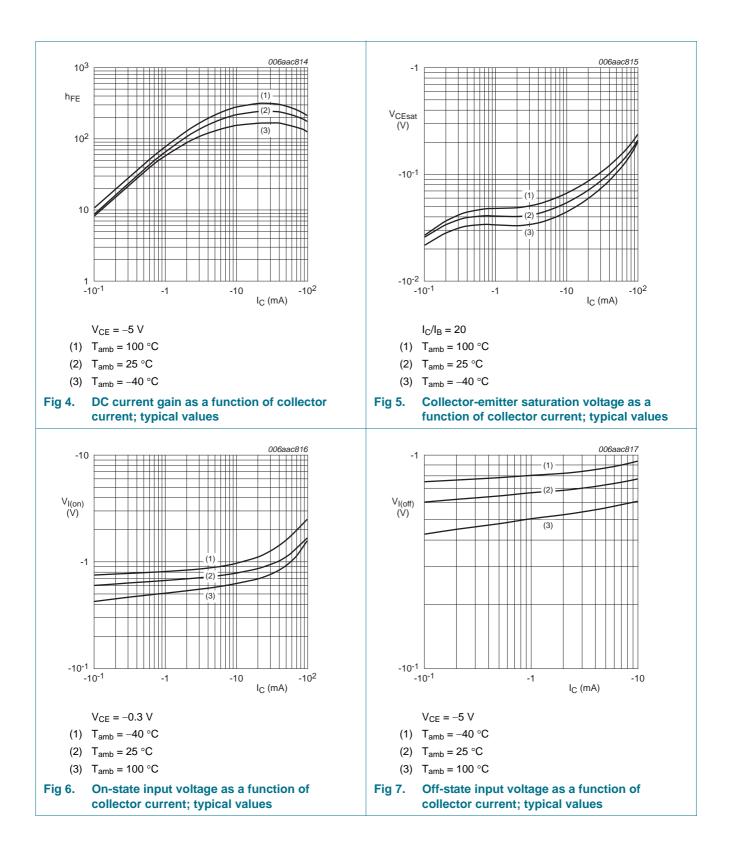
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per trans	istor						
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$		-	-	-100	nA
I _{CEO}	collector-emitter	V_{CE} = -30 V; I _B = 0 A		-	-	-100	nA
	cut-off current	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A};$ T _j = 150 °C		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-180	μA
h _{FE}	DC current gain	V_{CE} = -5 V; I_C = -10 mA		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -5 \text{ mA}; I_{B} = -0.25 \text{ mA}$		-	-	-100	mV
V _{I(off)}	off-state input voltage	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -100 \mu\text{A}$		-	-0.6	-0.5	V
V _{I(on)}	on-state input voltage	V_{CE} = –0.3 V; I_{C} = –5 mA		-1.1	-0.75	-	V
R1	bias resistor 1 (input)			1.54	2.20	2.86	kΩ
R2/R1	bias resistor ratio			17	21	26	
C _c	collector capacitance	$\label{eq:VCB} \begin{split} V_{CB} = -10 \ V; \ I_E = i_e = 0 \ A; \\ f = 1 \ MHz \end{split}$		-	-	3	pF
f _T	transition frequency	$V_{CB} = -5 \text{ V}; I_C = -10 \text{ mA};$ f = 100 MHz	<u>[1]</u>	-	180	-	MHz

[1] Characteristics of built-in transistor.

PEMB10_PUMB10 Product data sheet

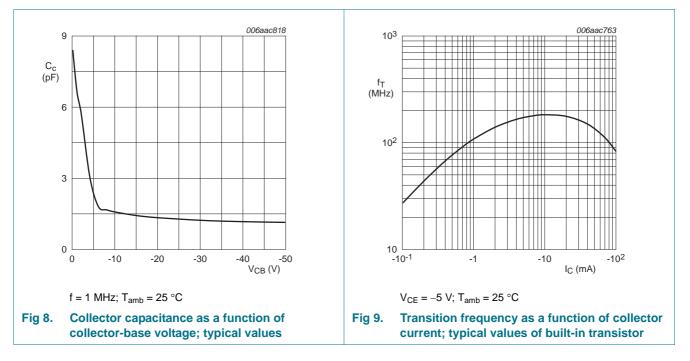
PEMB10; PUMB10

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



PEMB10; PUMB10

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



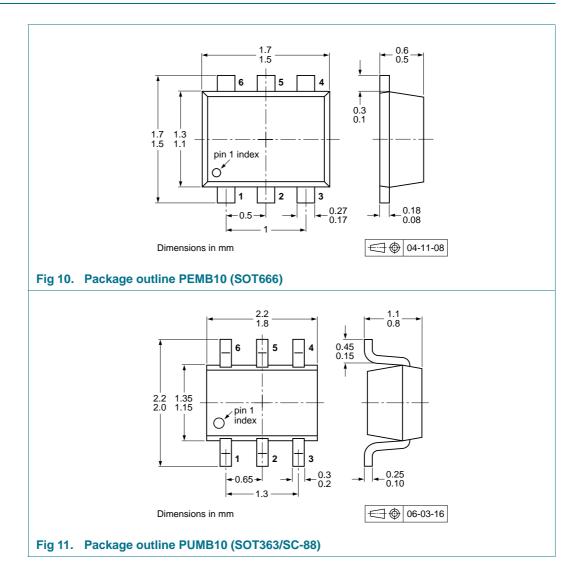
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

9. Package outline



PEMB10_PUMB10 Product data sheet

9 of 15

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

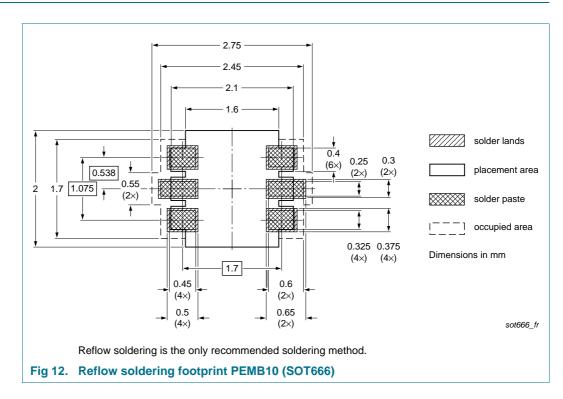
Type number	Package	Description		Packing quantity			
			3	3000	4000	8000	10000
PEMB10	SOT666	2 mm pitch, 8 mm tape and reel	-		-	-315	-
		4 mm pitch, 8 mm tape and reel	-		-115	-	-
PUMB10	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2] _	·115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3] _	·125	-	-	-165

[1] For further information and the availability of packing methods, see Section 14.

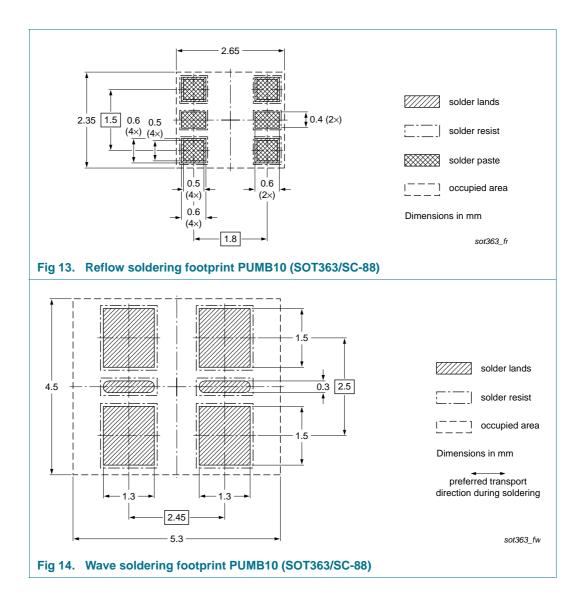
[2] T1: normal taping

[3] T2: reverse taping

11. Soldering



PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω



PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

12. Revision history

Table 10. Revision his	tory						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
PEMB10_PUMB10 v.3	20120103	Product data sheet	-	PEMB10_PUMB10 v.2			
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 						
	 Legal texts have been adapted to the new company name where appropriate. 						
	<u>Section 1 "Product profile"</u> : updated						
	 <u>Section 4 "Marking"</u>: updated 						
	 <u>Table 7 "Thermal characteristics</u>": updated according to the latest measurements 						
	 <u>Table 8 "Characteristics</u>": I_{CEO} updated according to the latest measurements, f_T added, V_{i(off)} redefined to V_{I(off)} off-state input voltage, V_{i(on)} redefined to V_{I(on)} on-state input voltage. 						
	• Figure 1 to 9: added						
	 <u>Section 8 "Test information"</u>: added 						
	 Figure 10 and <u>11</u>: replaced by minimized package outline drawings 						
	 <u>Section 10 "Packing information"</u>: added 						
	 Section 11 "S 	 <u>Section 11 "Soldering"</u>: added 					
	 Section 13 "L 	egal information": updated					
PEMB10_PUMB10 v.2	20031003	Product data sheet	-	PEMB10 v.1			
PEMB10 v.1	20010914	Preliminary specification	on -	-			

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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PEMB10; PUMB10

PNP/PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 47 k Ω

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